

ABSTRACT OF THE DISCLOSURE

A semiconductor element is formed in a semiconductor wafer, and a groove is formed by performing half-cut dicing on the semiconductor wafer 5 along a dicing line. A dicing region of the semiconductor wafer is irradiated with a laser beam to melt or vaporize a cutting streak formed by dicing. An adhesive tape is adhered to the semiconductor element formation surface of the semiconductor wafer, and the 10 other side of the semiconductor element formation surface is ground to at least a depth reaching the groove.